

Amendments to the Claims

1. (CURRENTLY AMENDED) A method for the manufacture of a display comprising
_____providing a substrate
_____depositing a removable layer to said substrate covering at least a part of said substrate,
characterized in
_____depositing an etch and temperature resistant layer on said removable layer, essentially covering said removable layer,
_____processing a display on at least part of said etch and temperature resistant layer, and
_____removing said removable layer by etching with an etchant, said etch and temperature resistant layer preventing the etchant from making contact with said display.
2. (ORIGINAL) A method according to claim 1, wherein said substrate is provided with etch openings and said etching is performed by leading an etchant through the substrate through said etch openings.
3. (CURRENTLY AMENDED) A method according to ~~claim 1 or 2~~claim 1, wherein said substrate comprises a silicon material.
4. (ORIGINAL) A method according to claim 4, wherein said substrate comprises polysilicon plates.
5. (ORIGINAL) A method according to claim 4, wherein said substrate comprises silicon microsieves.
6. (ORIGINAL) A method according to claim 4, wherein said substrate comprises a silicon wafer.

7. (CURRENTLY AMENDED) A method according to ~~any one of the preceding claims~~claim 1, wherein said substrate has a height profile which can be passed on to the display.
8. (CURRENTLY AMENDED) A method according to ~~any one of the preceding claims~~claim 1, wherein said etch and temperature resistant layer comprises Si_3N_4 .
9. (CURRENTLY AMENDED) A method according to ~~any one of the preceding claims~~claim 1, wherein said etch and temperature resistant layer comprises stacks of Si_3N_4 and SiO_2 .
10. (CURRENTLY AMENDED) A method according to ~~any one of the preceding claims~~claim 1, wherein said etch and temperature resistant layer comprises SiON.
11. (CURRENTLY AMENDED) A method according to ~~any one of the preceding claims~~claim 1, wherein said etch and temperature resistant layer comprises stacks of Si_3N_4 and SiON.
12. (CURRENTLY AMENDED) A method according to ~~any one of the preceding claims~~claim 1, wherein said etch and temperature resistant layer comprises stacks of stacks of SiO_2 and SiON.
13. (CURRENTLY AMENDED) A method according to ~~any one of the preceding claims~~claim 1, wherein said etch and temperature resistant layer comprises stacks of Si_3N_4 , SiO_2 and SiON.
14. (CURRENTLY AMENDED) A method according to ~~any one of the preceding claims~~claim 1, wherein said removable layer comprises SiO_2 .
15. (CURRENTLY AMENDED) A method according to ~~any one of the preceding claims~~claim 1, wherein said etchant comprises a HF-solution.

16. (CURRENTLY AMENDED) A method according to ~~any one of the preceding~~claim 1, wherein said etchant comprises $\text{NH}_4\text{F}:\text{HF}$.
17. (CURRENTLY AMENDED) A display obtainable using the method according to ~~any one of the preceding claims~~claim 1.
18. (CURRENTLY AMENDED) A method according to ~~any one of the preceding claims~~claim 1 for non display applications, e.g. plastic electronics, MEMS, and Passive Integration.